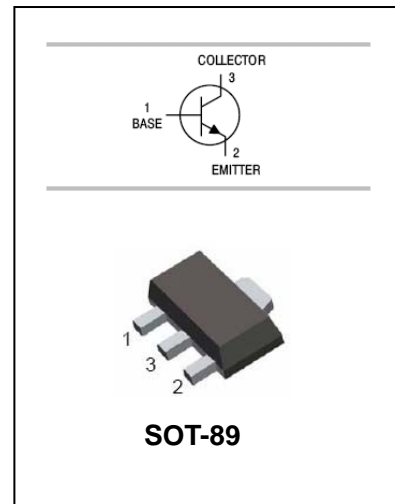


SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

FEATURES

- Charger-up time is about 1 mS faster Than of a germanium transistor.
- Small saturation voltage can bring dissipation And flasing times.



ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| HM879 | 879 | SOT-89 |

MAXIMUM RATING @ Ta=25°C unless otherwise specified

| Symbol | Parameter | Value | Units |
|----------------|---|---------|-------|
| V_{CBO} | Collector-Base Voltage | 30 | V |
| V_{CEX} | Collector-Emitter Voltage | 20 | V |
| V_{CEO} | Collector-Emitter Voltage | 10 | V |
| V_{EBO} | Emitter-Base Voltage | 6 | V |
| I_C | Collector Current –Continuous –Pluse | 3 5 | A |
| P_C | Collector Dissipation | 1 | W |
| T_j, T_{stg} | Junction and Storage Temperature | -55~150 | °C |

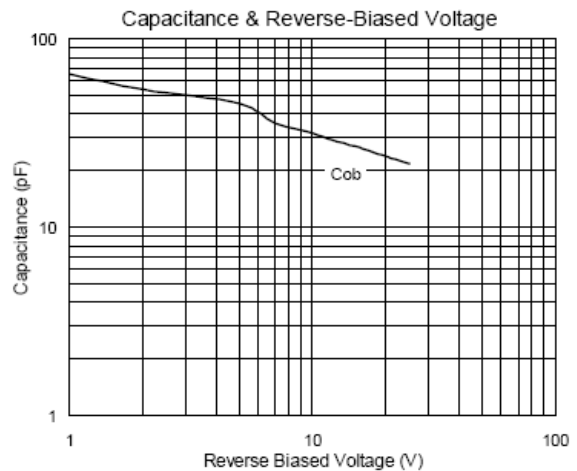
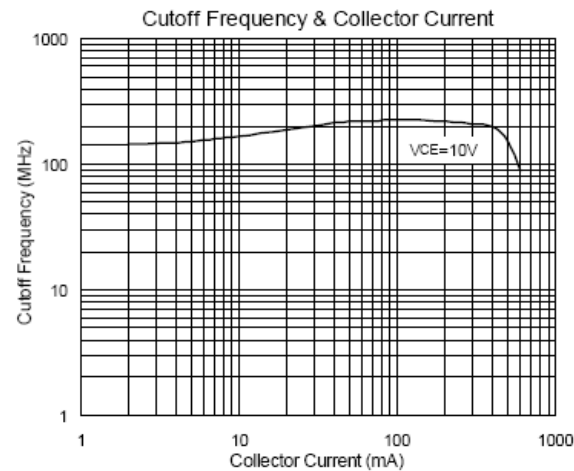
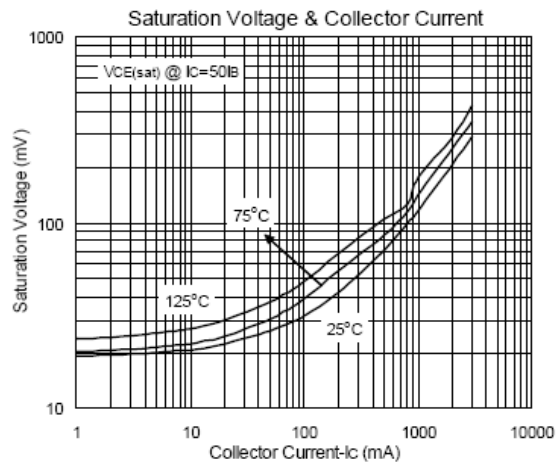
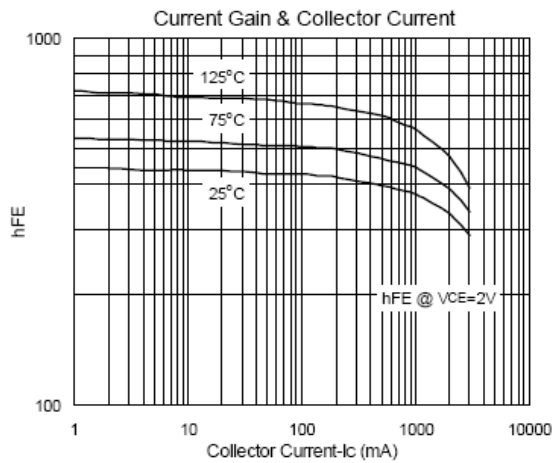
SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|--------------------------------------|---------------|-----------------------------|-----|-----|-----|------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=10\mu A, I_E=0$ | 30 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=1mA, I_B=0$ | 10 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=10\mu A, I_C=0$ | 6 | | | V |
| Collector to Emitter Voltage | $V_{(BR)CEX}$ | $I_C=1mA, V_{BE}=3V$ | 20 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=20V, I_E=0$ | | | 100 | nA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=4V, I_C=0$ | | | 100 | nA |
| DC current gain | h_{FE} | $V_{CE}=2V, I_C=3A$ | 140 | 210 | 400 | |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=3A, I_B=60mA$ | | 0.3 | 0.4 | V |
| Transition frequency | f_T | $V_{CE}=10V, I_C=50mA$ | | 200 | | MHz |
| Collector output capacitance | C_{ob} | $V_{CB}=10V, I_E=0, f=1MHz$ | | 30 | | pF |

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



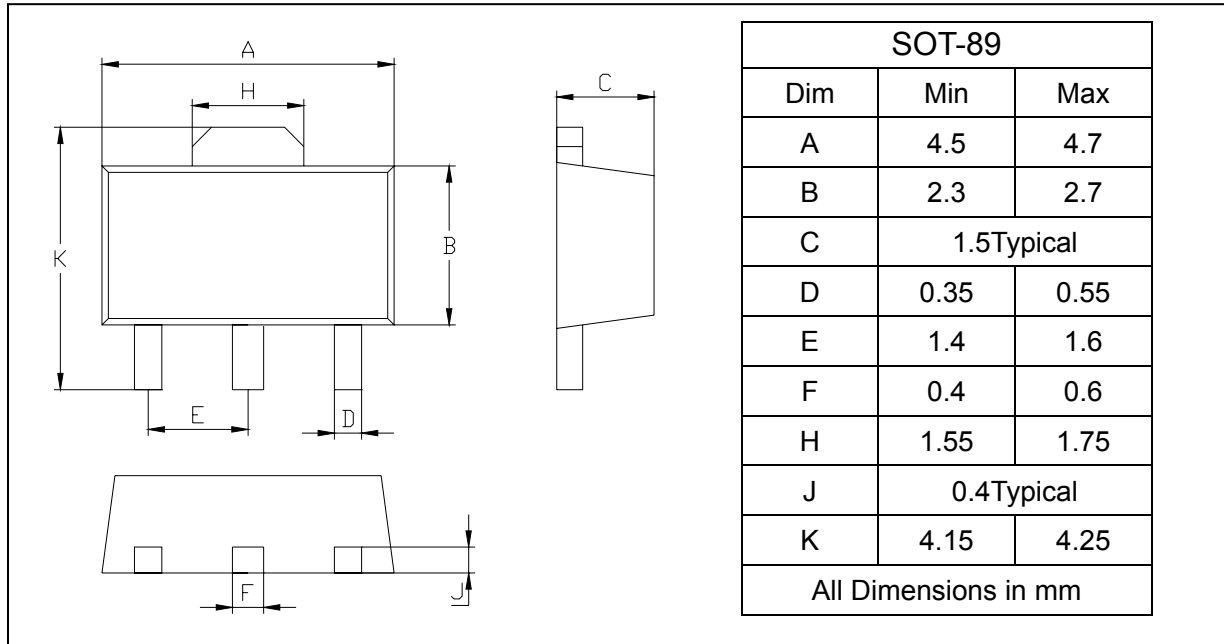
SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

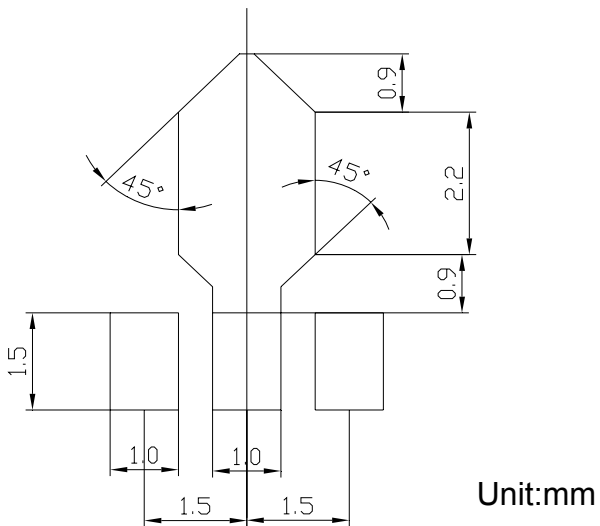
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

| Device | Package | Shipping |
|--------|---------|----------------|
| HM879 | SOT-89 | 1000/Tape&Reel |